

# SIEMENS

Industrial Solutions and Services



## IBIS Models with Reactive Loads

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## Overview

### Motivation

### Arpad's conclusion

### Superposition

### Summary

#### □ Motivation

#### □ Arpad's conclusion to the „Accuracy of IBIS models with reactive loads“ (IBIS Summit Santa Clara 2006)

#### □ What to do, if the load is reactive?

##### ➤ Transistor Model

##### ➤ IBIS Model

#### □ Approach by superposition of models / WF with X-loads

#### □ Summary



## Requirements from automotive industry

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### ❑ Request for using IBIS Models

- IEEE-Standard
- SI / EMC – tools

### ❑ Automotive specific environment

- + low frequencies
- + moderate voltage slopes
- - high voltage swing and high currents
- - reactive loads (coils, motors)
- - cable as transmission line

### ❑ Focus on EM radiation and susceptibility



## IBIS-model vs. HSPICE and Measurement in the → Time domain

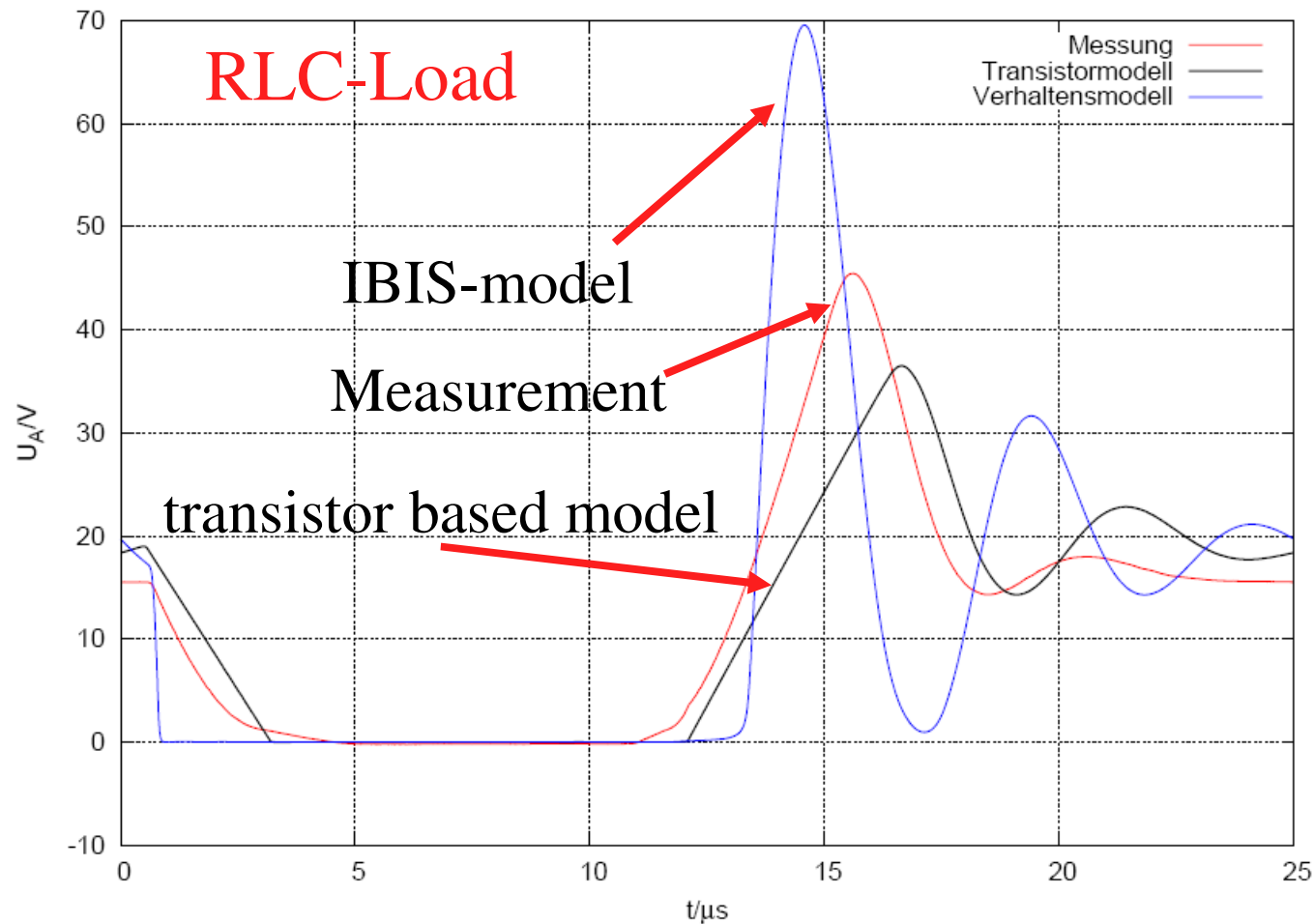
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from Dr.-Ing. U. Neibig – R. Bosch GmbH, @ EMV2006

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## → Frequency domain

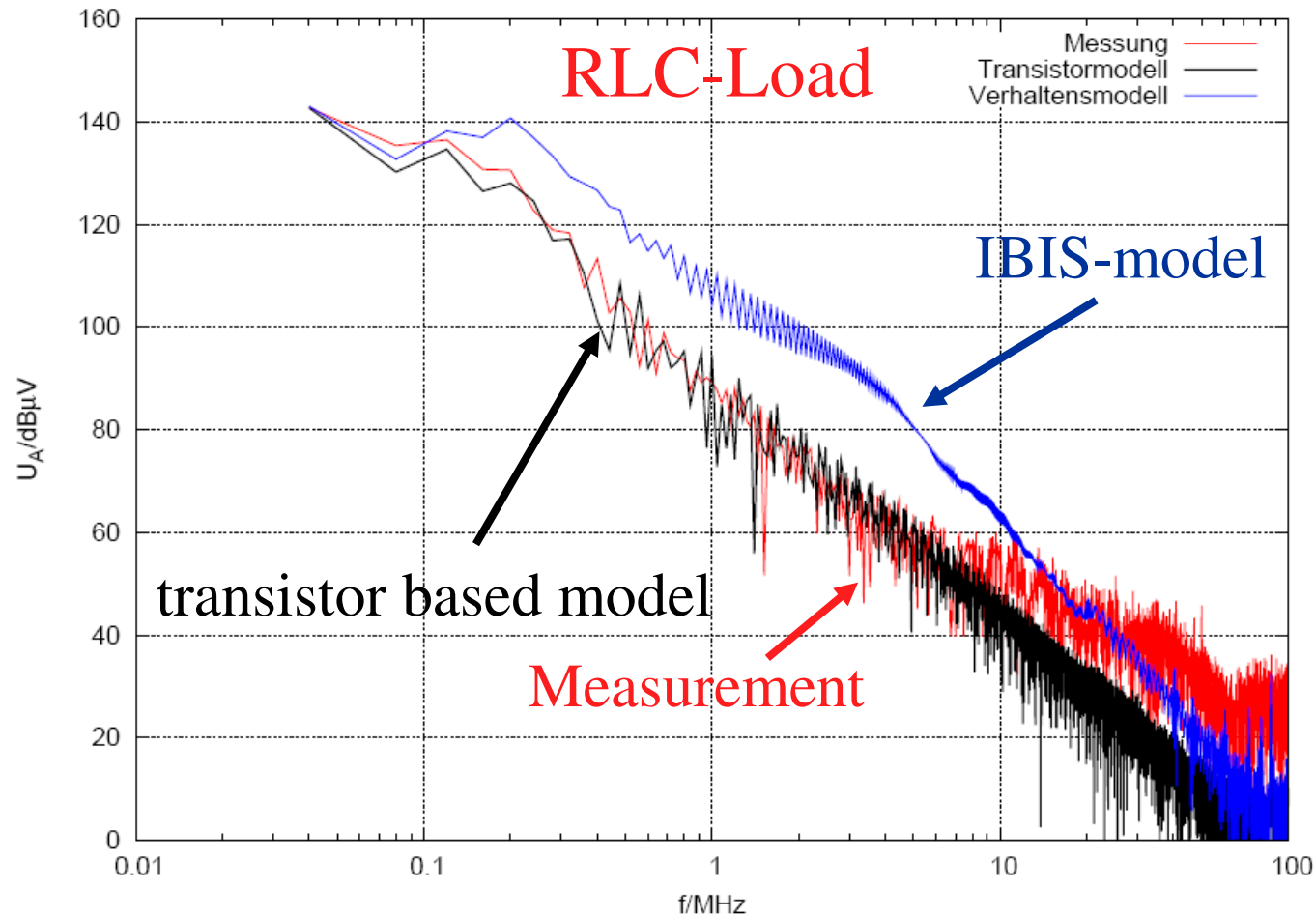
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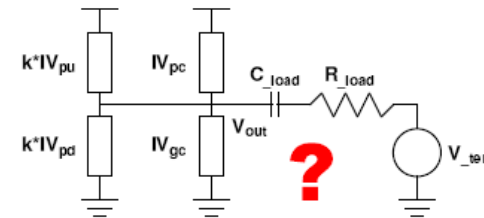
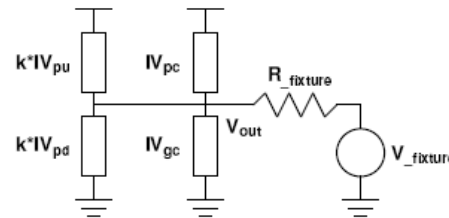
# IBIS Models inadequate for Reactive Loads

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Arpad Muranyi – DesignCon. Santa Clara 2006

## Problem statement



$$0 = k_{pu}(t) \cdot IV_{pu}(V_{wfm1}(t)) + IV_{pc}(V_{wfm1}(t)) - k_{pd}(t) \cdot IV_{pd}(V_{wfm1}(t)) - IV_{gc}(V_{wfm1}(t)) - I_{out}(V_{wfm1}(t))$$

$$0 = k_{pu}(t) \cdot IV_{pu}(V_{wfm2}(t)) + IV_{pc}(V_{wfm2}(t)) - k_{pd}(t) \cdot IV_{pd}(V_{wfm2}(t)) - IV_{gc}(V_{wfm2}(t)) - I_{out}(V_{wfm2}(t))$$

where

$$I_{out} = \frac{V_{out} - V_{fixture}}{R_{fixture}}$$

**dV/dt and/or dI/dt are missing from this equation**

**The current of the capacitor is**  
 **$I = C \cdot dV/dt$**

**The voltage of an inductor is**  
 **$V = L \cdot dI/dt$**

$$I_{out} \neq \frac{V_{out} - V_{fixture}}{R_{fixture}}$$



\*Other brands and names are the property of their respective owners

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## Approach for Superposition of Reactive WF

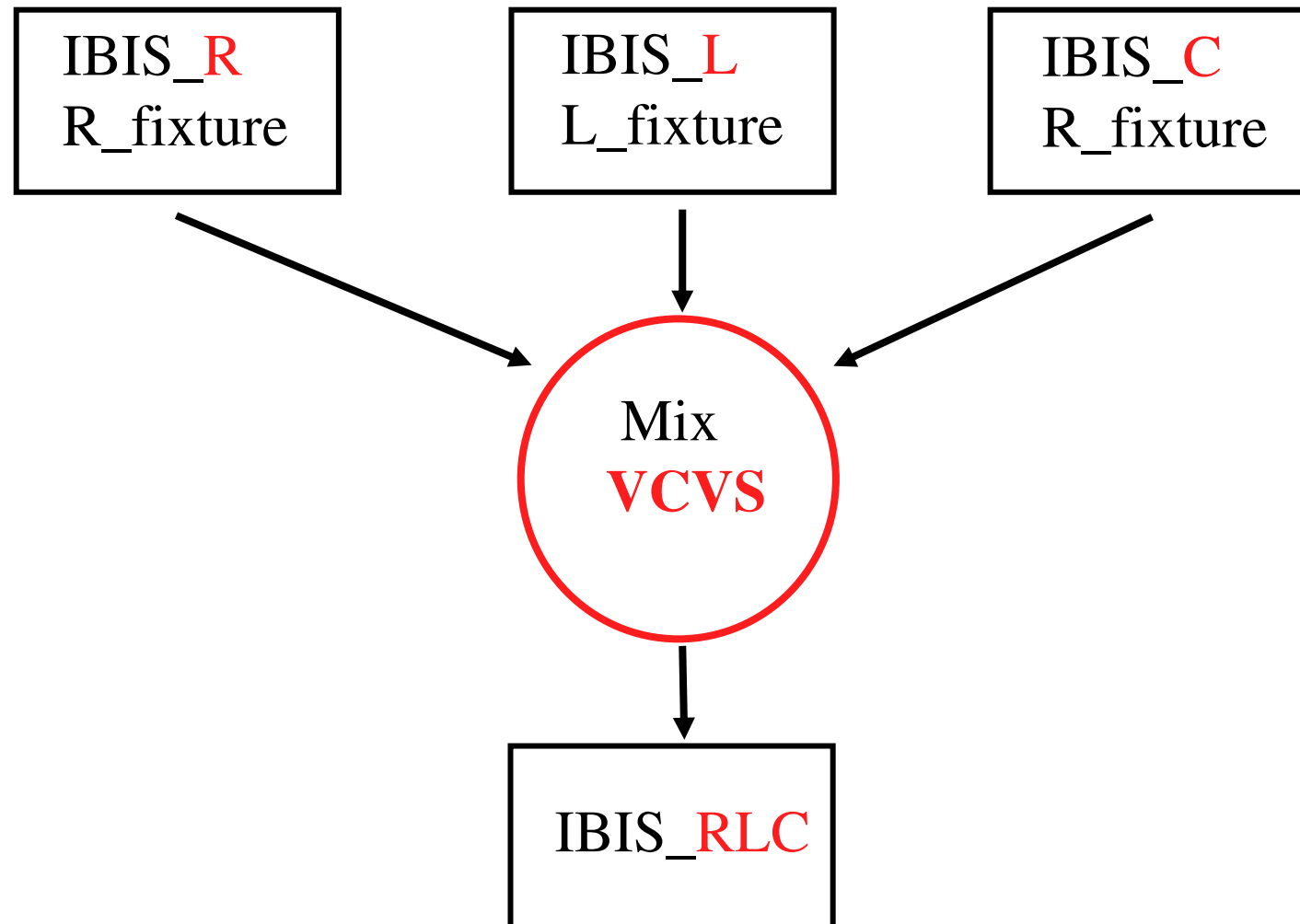
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# WF with X-load vs. Transistor based model

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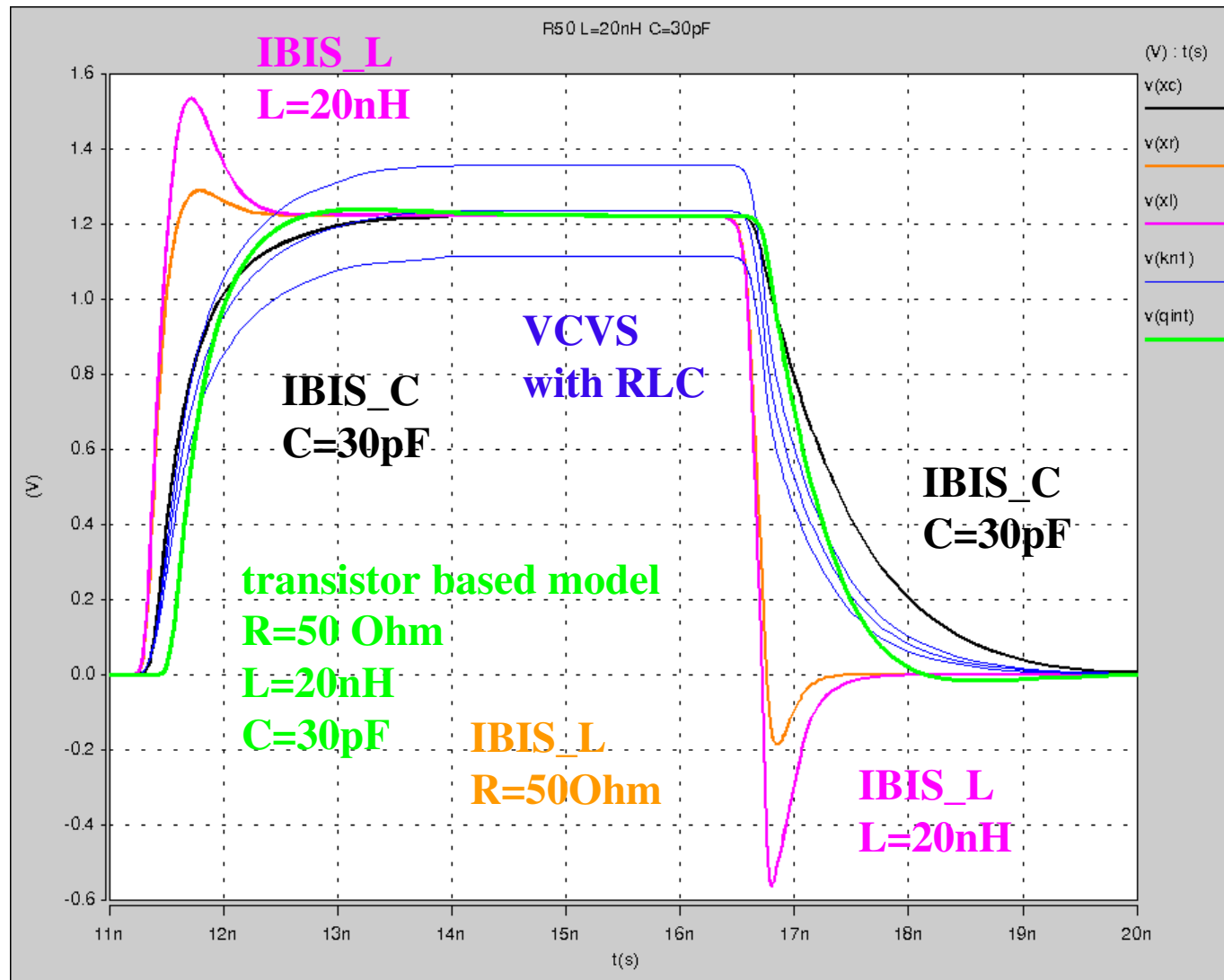
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# WF with X-load vs. Transistor based model (zoom)

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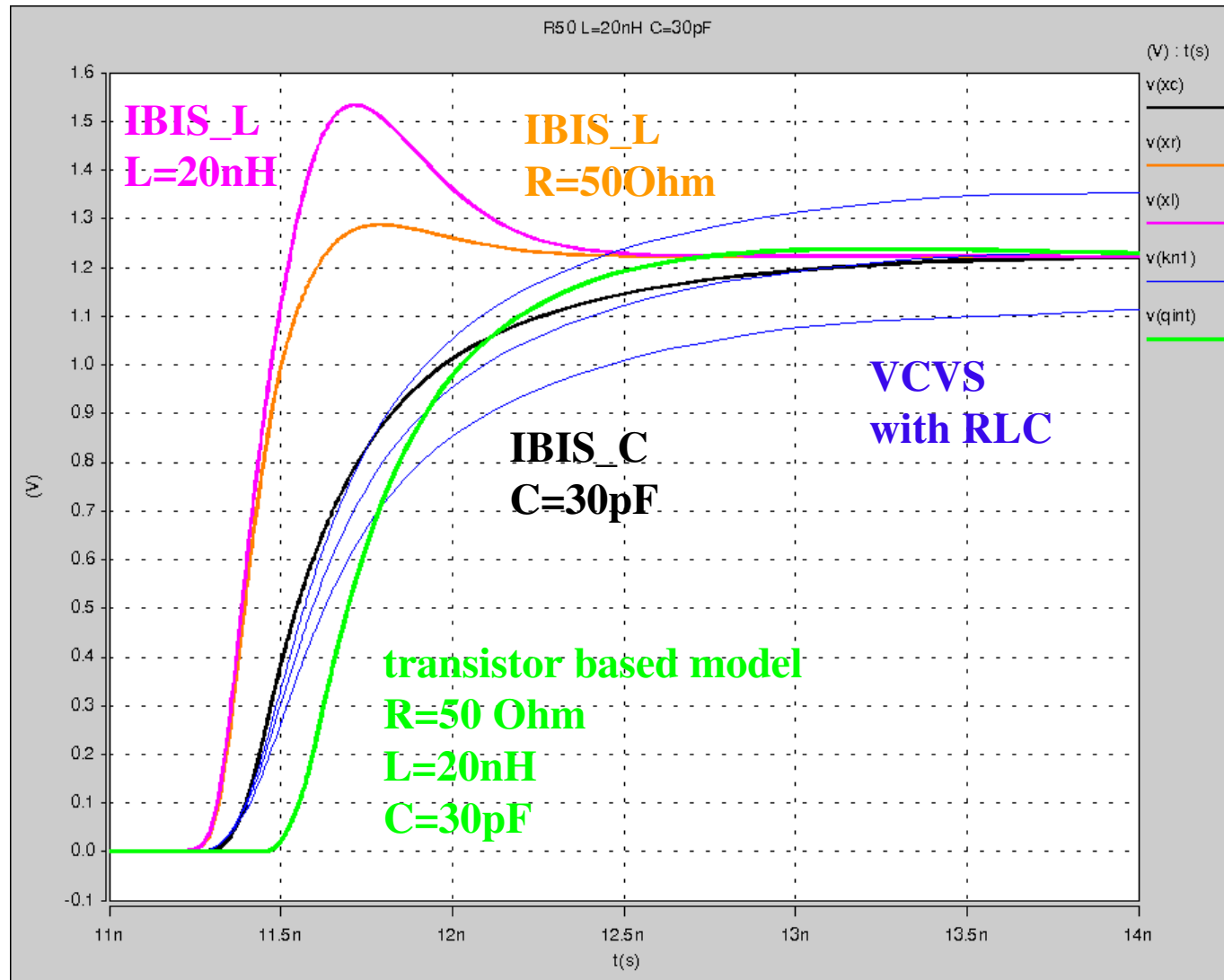
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# WF with X-load vs. Transistor based model (zoom)

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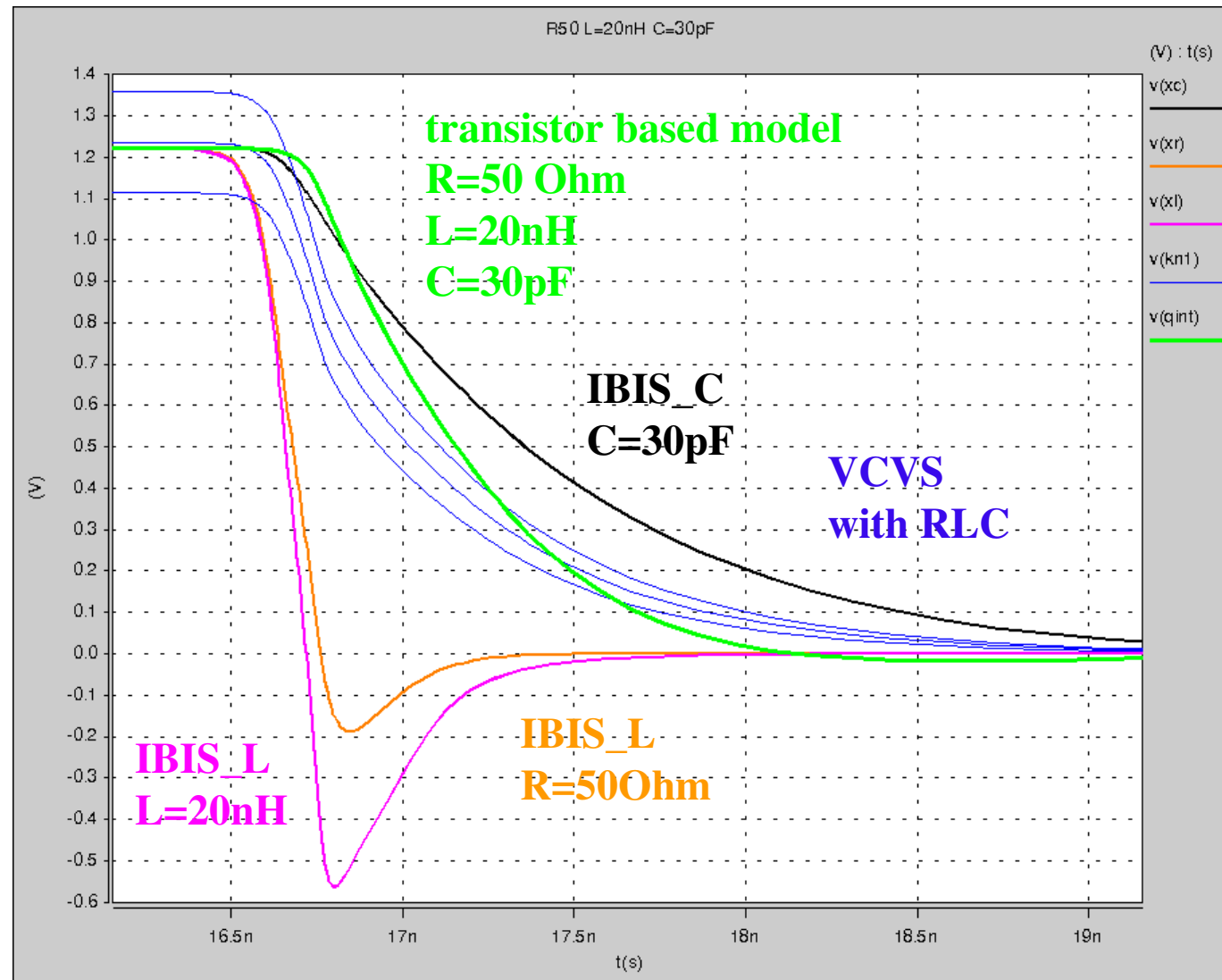
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- ❑ IF the IBIS models with the same reactive load, as the application
  - ➔ fitting results
  - but
    - ❖ not practicable ➔ huge # of models/waveforms
    - ❖ slightly different X-load ➔ unpredictable results
- ❑ By superposition of different models with X-loads
  - **NO** simple, unique way to the solution
  - more investigation has to be done
- ❑ Reactive Loads can be actually described by:
  - ❑ Transistor models
  - ❑ VHDL-AMS

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## IBIS Models with Reactive Loads

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Questions